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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	47
Program Memory Size	24KB (24K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21355cnfp-x6

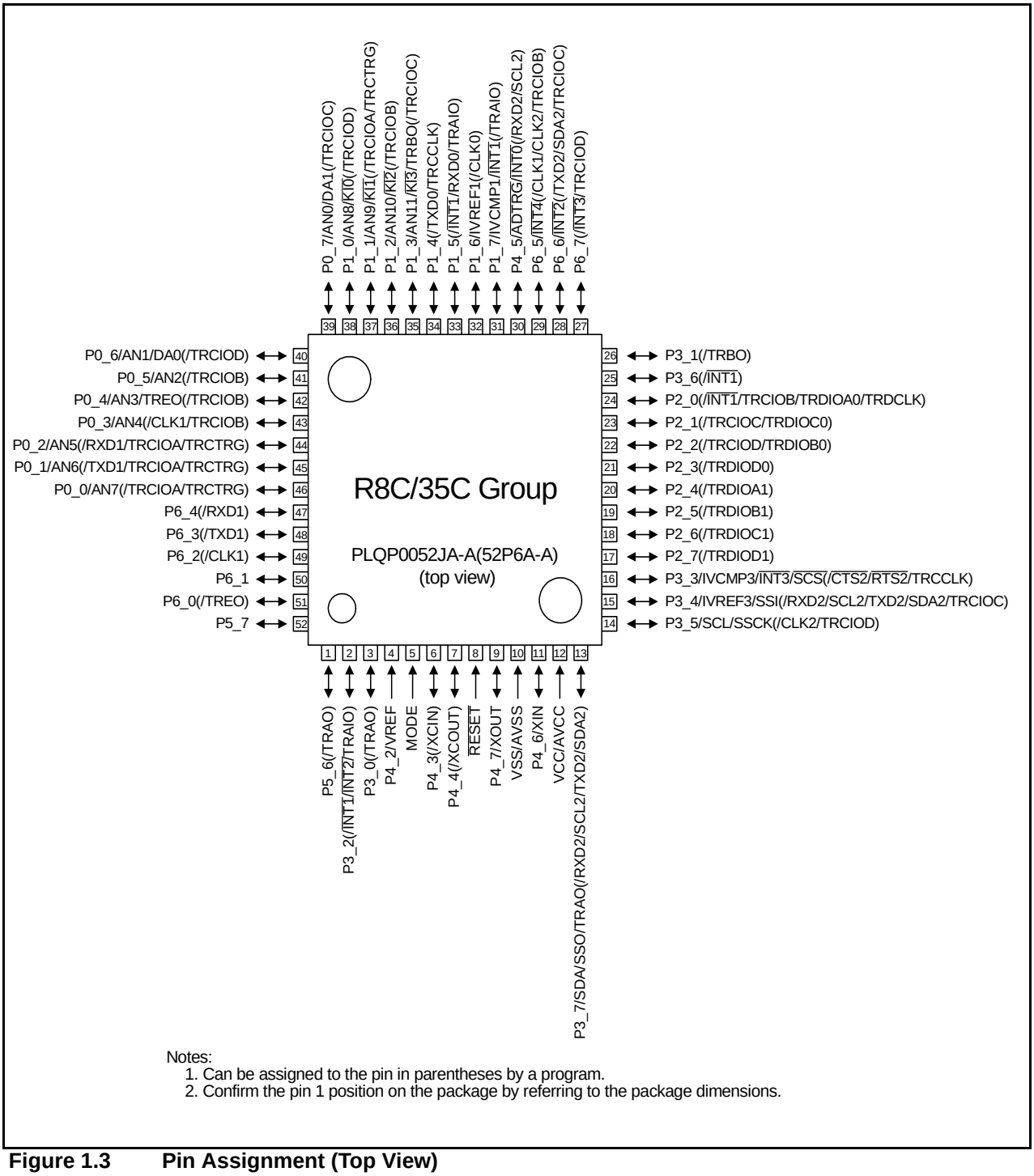
Table 1.2 Specifications for R8C/35C Group (2)

Item	Function	Specification
Serial Interface	UART0, UART1	Clock synchronous serial I/O/UART × 2 channel
	UART2	Clock synchronous serial I/O/UART, I²C mode (I²C-bus), multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I²C-bus)
I²C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 12 channels, includes sample and hold function, with sweep mode
D/A Converter		8-bit resolution × 2 circuits
Comparator B		2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • Background operation (BGO) function
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 1.8 to 5.5 V)
Current consumption		Typ. 6.5 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 3.5 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) Typ. 2.0 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version) (1)
Package		52-pin LQFP Package code: PLQP0052JA-A (previous code: 52P6A-A)

Note:
1. Specify the D version if D version functions are to be used.

1.4 Pin Assignment

Figure 1.3 shows the Pin Assignment (Top View). Tables 1.4 and 1.5 outline the Pin Name Information by Pin Number.



Notes:
1. Can be assigned to the pin in parentheses by a program.
2. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.3 Pin Assignment (Top View)

Table 1.4 Pin Name Information by Pin Number (1)

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator B
1		P5_6		(TRAO)				
2		P3_2	($\overline{INT1}$/$\overline{INT2}$)	(TRAIO)				
3		P3_0		(TRAO)				
4		P4_2						VREF
5	MODE							
6	(XCIN)	P4_3						
7	(XCOUT)	P4_4						
8	$\overline{RESET}$							
9	XOUT	P4_7						
10	VSS/AVSS							
11	XIN	P4_6						
12	VCC/AVCC							
13		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
14		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
15		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
16		P3_3	$\overline{INT3}$	(TRCCLK)	($\overline{CTS2}$/$\overline{RTS2}$)	$\overline{SCS}$		IVCMP3
17		P2_7		(TRDIOD1)				
18		P2_6		(TRDIOC1)				
19		P2_5		(TRDIOB1)				
20		P2_4		(TRDIOA1)				
21		P2_3		(TRDIOD0)				
22		P2_2		(TRCIOD/ TRDIOB0)				
23		P2_1		(TRCIOC/ TRDIOC0)				
24		P2_0	($\overline{INT1}$)	(TRCIOB/ TRDIOA0/ TRDCLK)				
25		P3_6	($\overline{INT1}$)					
26		P3_1		(TRBO)				
27		P6_7	($\overline{INT3}$)	(TRCIOD)				
28		P6_6	$\overline{INT2}$	(TRCIOC)	(TXD2/SDA2)			
29		P6_5	$\overline{INT4}$	(TRCIOB)	(CLK1/CLK2)			
30		P4_5	$\overline{INT0}$		(RXD2/SCL2)			$\overline{ADTRG}$
31		P1_7	$\overline{INT1}$	(TRAIO)				IVCMP1
32		P1_6			(CLK0)			IVREF1
33		P1_5	($\overline{INT1}$)	(TRAIO)	(RXD0)			
34		P1_4		(TRCCLK)	(TXD0)			
35		P1_3	$\overline{KI3}$	TRBO (/TRCIOC)				AN11

Note:
1. Can be assigned to the pin in parentheses by a program.

1.5 Pin Functions

Tables 1.6 and 1.7 list Pin Functions.

Table 1.6 Pin Functions (1)

Item	Pin Name	I/O Type	Description
Power supply input	VCC, VSS	–	Apply 1.8 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	–	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins (1). To use an external clock, input it to the XOUT pin and leave the XIN pin open.
XIN clock output	XOUT	I/O	
XCIN clock input	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins (1). To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT4}}$	I	$\overline{\text{INT}}$ interrupt input pins. $\overline{\text{INT0}}$ is timer RB, RC and RD input pin.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAIO	I/O	Timer RA I/O pin
	TRAO	O	Timer RA output pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCCLK	I	External clock input pin
	TRCTRG	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Timer RC I/O pins
Timer RD	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1	I/O	Timer RD I/O pins
	TRDCLK	I	External clock input pin
Timer RE	TREO	O	Divided clock output pin
Serial interface	CLK0, CLK1, CLK2	I/O	Transfer clock I/O pins
	RXD0, RXD1, RXD2	I	Serial data input pins
	TXD0, TXD1, TXD2	O	Serial data output pins
	$\overline{\text{CTS2}}$	I	Transmission control input pin
	$\overline{\text{RTS2}}$	O	Reception control output pin
	SCL2	I/O	I^2C mode clock I/O pin
	SDA2	I/O	I^2C mode data I/O pin
I^2C bus	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
SSU	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin

I: Input O: Output I/O: Input and output

Note:

1. Refer to the oscillator manufacturer for oscillation characteristics.

Table 1.7 Pin Functions (2)

Item	Pin Name	I/O Type	Description
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter and D/A converter
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
	$\overline{\text{ADTRG}}$	I	A/D external trigger input pin
D/A converter	DA0, DA1	O	D/A converter output pins
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins
	IVREF1, IVREF3	I	Comparator B reference voltage input pins
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_3 to P4_7, P5_6, P5_7, P6_0 to P6_7	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. All ports can be used as LED drive ports.
Input port	P4_2	I	Input-only port

I: Input O: Output I/O: Input and output

Table 4.10 SFR Information (10) (1)

Address	Register	Symbol	After Reset
2C70h	DTC Control Data 6	DTCD6	XXh
2C71h			XXh
2C72h			XXh
2C73h			XXh
2C74h			XXh
2C75h			XXh
2C76h			XXh
2C77h			XXh
2C78h	DTC Control Data 7	DTCD7	XXh
2C79h			XXh
2C7Ah			XXh
2C7Bh			XXh
2C7Ch			XXh
2C7Dh			XXh
2C7Eh			XXh
2C7Fh			XXh
2C80h	DTC Control Data 8	DTCD8	XXh
2C81h			XXh
2C82h			XXh
2C83h			XXh
2C84h			XXh
2C85h			XXh
2C86h			XXh
2C87h			XXh
2C88h	DTC Control Data 9	DTCD9	XXh
2C89h			XXh
2C8Ah			XXh
2C8Bh			XXh
2C8Ch			XXh
2C8Dh			XXh
2C8Eh			XXh
2C8Fh			XXh
2C90h	DTC Control Data 10	DTCD10	XXh
2C91h			XXh
2C92h			XXh
2C93h			XXh
2C94h			XXh
2C95h			XXh
2C96h			XXh
2C97h			XXh
2C98h	DTC Control Data 11	DTCD11	XXh
2C99h			XXh
2C9Ah			XXh
2C9Bh			XXh
2C9Ch			XXh
2C9Dh			XXh
2C9Eh			XXh
2C9Fh			XXh
2CA0h	DTC Control Data 12	DTCD12	XXh
2CA1h			XXh
2CA2h			XXh
2CA3h			XXh
2CA4h			XXh
2CA5h			XXh
2CA6h			XXh
2CA7h			XXh
2CA8h	DTC Control Data 13	DTCD13	XXh
2CA9h			XXh
2CAAh			XXh
2CABh			XXh
2CACh			XXh
2CADh			XXh
2CAEh			XXh
2CAFh			XXh

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	–40°C ≤ T_{opr} ≤ 85°C	500	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version) / –40 to 85 (D version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

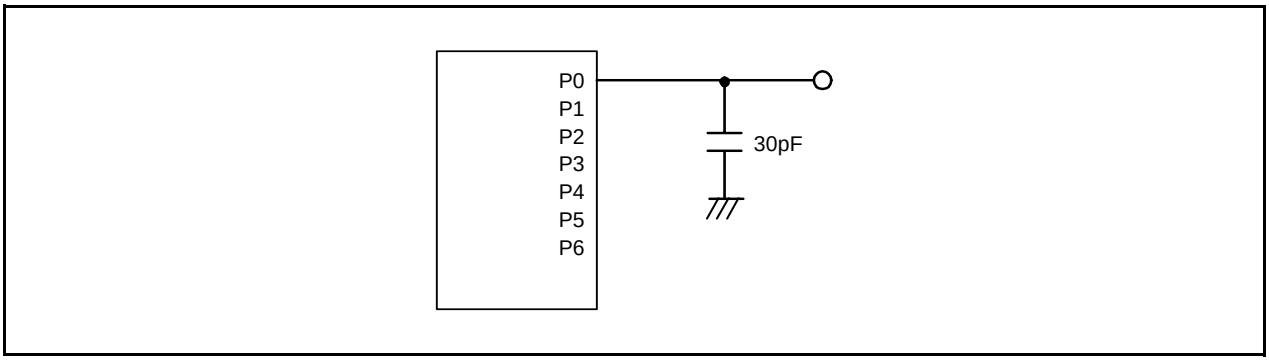


Figure 5.1 Ports P0 to P6 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}		–	–	10	Bit
–	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	5	MHz
–	Tolerance level impedance				–	3	–	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
I_{Vref}	V_{ref} current		V_{CC} = 5 V, XIN = f1 = ϕAD = 20 MHz		–	45	–	µA
V_{ref}	Reference voltage				2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	–	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.6 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		1,000 (3)	–	–	times
–	Byte program time		–	80	500	µs
–	Block erase time		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5+CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time (7)	Ambient temperature = 55°C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
–	Voltage detection 0 circuit response time (4)	At the falling of V_{CC} from 5 V to (Vdet0_0 – 0.1) V	–	6	150	µs
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	1.5	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of Vcc	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of Vcc	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of Vcc	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of Vcc	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of Vcc	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of Vcc	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of Vcc	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of Vcc	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of Vcc	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of Vcc	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of Vcc	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of Vcc	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of Vcc	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of Vcc	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of Vcc	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of Vcc	4.20	4.45	4.75	V
–	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	–	0.07	–	V
		Vdet1_6 to Vdet1_F selected	–	0.10	–	V
–	Voltage detection 1 circuit response time (3)	At the falling of V_{CC} from 5 V to (Vdet1_0 – 0.1) V	–	60	150	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	38.4	40	41.6	MHz
		V_{CC} = 1.8 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	35.389	36.864	38.338	MHz
		V_{CC} = 1.8 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	30.72	32	33.28	MHz
		V_{CC} = 1.8 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C	30.40	32	33.60	MHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	0.5	3	ms
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	400	–	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	30	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	2	–	µA

Note:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		–	–	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.15 Timing Requirements of Synchronous Serial Communication Unit (SSU) (1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC} (2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC} (2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC} (2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	$1.5t_{CYC}$ + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	$1.5t_{CYC}$ + 200	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

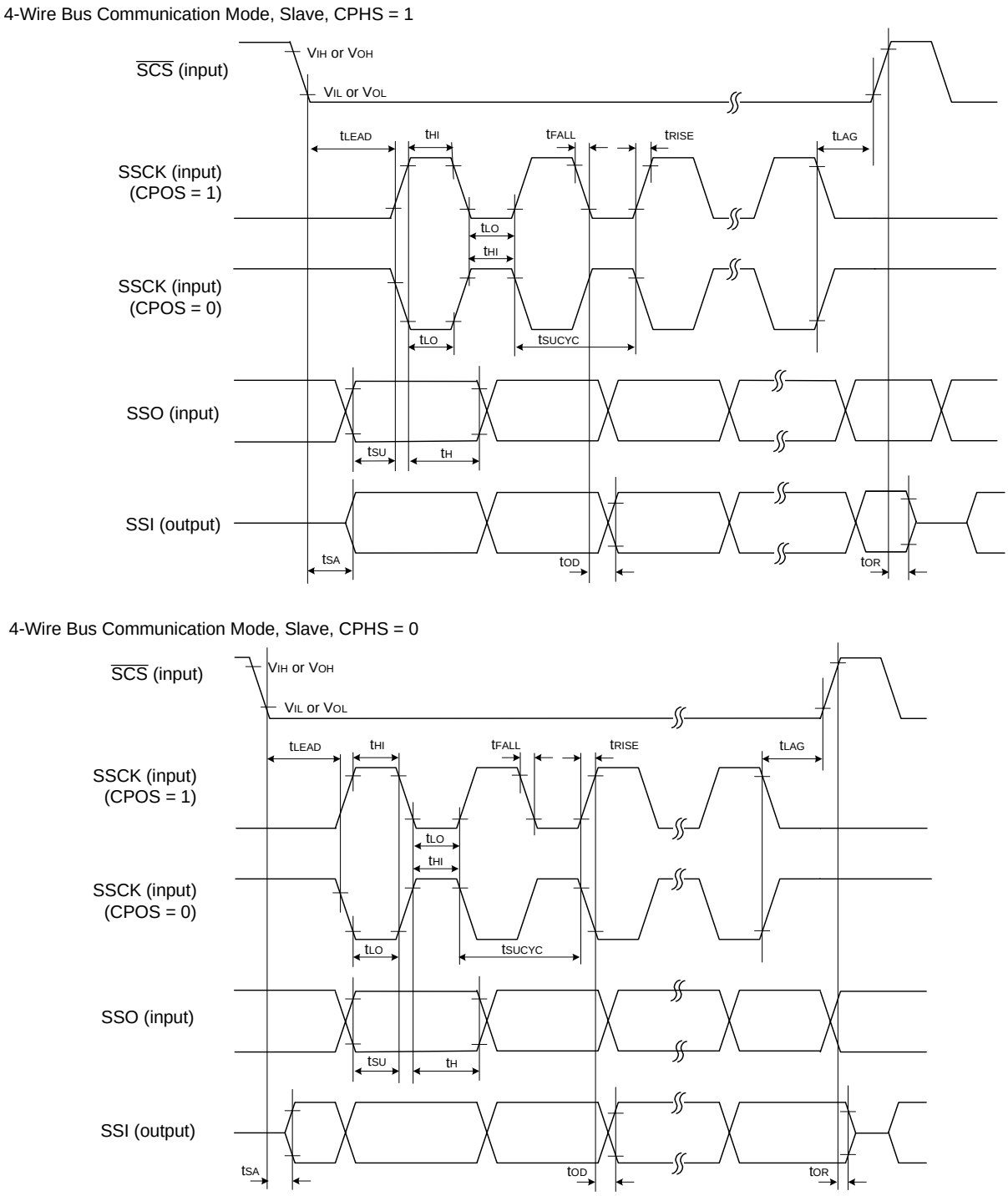


Figure 5.5 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

Table 5.18 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.2	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0	–	85	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	47	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1, Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1, Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0 (1) 15 (2)	–	µA

Notes:
1. Value when the program ROM capacity of the product is 16 Kbytes to 32 Kbytes.
2. Value when the program ROM capacity of the product is 48 Kbytes to 128 Kbytes.

Table 5.23 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 3.0 V		0.1	0.4	–	V
		$\overline{RESET}$	V_{CC} = 3.0 V		0.1	0.5	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3.0 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3.0 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 2.7 V ≤ V_{CC} < 4.2 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.24 Electrical Characteristics (4) [2.7 V ≤ Vcc < 3.3 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0	–	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0 (1) 15 (2)	–	µA

Notes:
1. Value when the program ROM capacity of the product is 16 Kbytes to 32 Kbytes.
2. Value when the program ROM capacity of the product is 48 Kbytes to 128 Kbytes.

Timing Requirements
(Unless Otherwise Specified: Vcc = 3 V, Vss = 0 V at Topr = 25°C)

Table 5.25 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

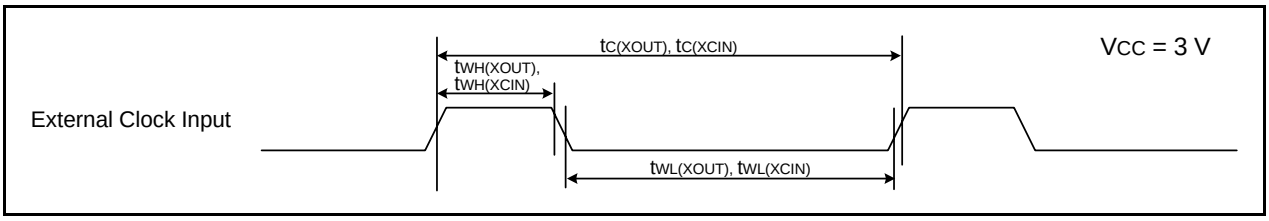


Figure 5.12 External Clock Input Timing Diagram when VCC = 3 V

Table 5.26 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

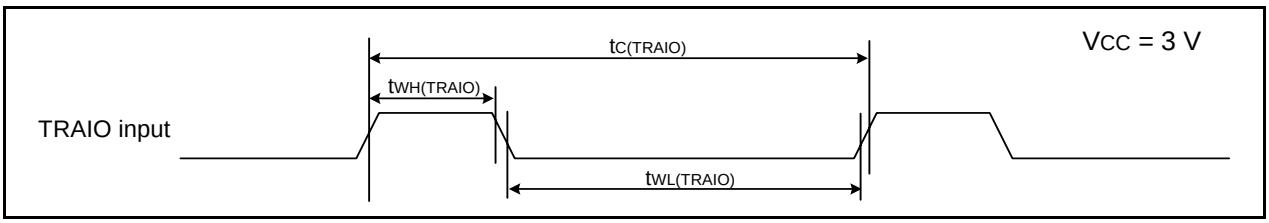


Figure 5.13 TRAIO Input Timing Diagram when Vcc = 3 V

Table 5.33 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	–	ns
$t_{W(CKH)}$	CLKi input “H” width	400	–	ns
$t_{W(CKL)}$	CLKi input “L” width	400	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	150	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 to 2

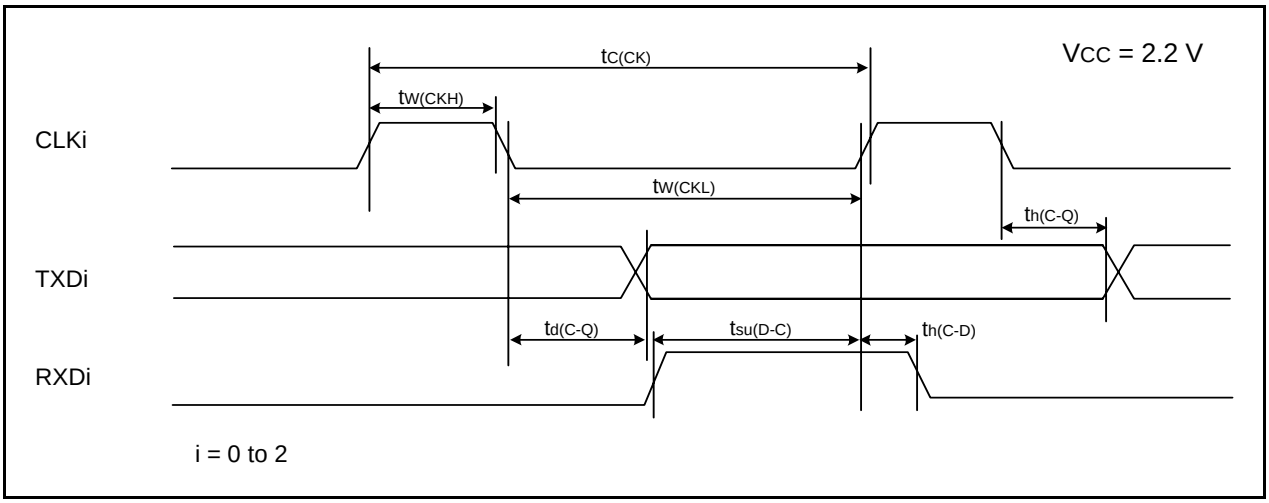


Figure 5.18 Serial Interface Timing Diagram when VCC = 2.2 V

Table 5.34 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	–	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

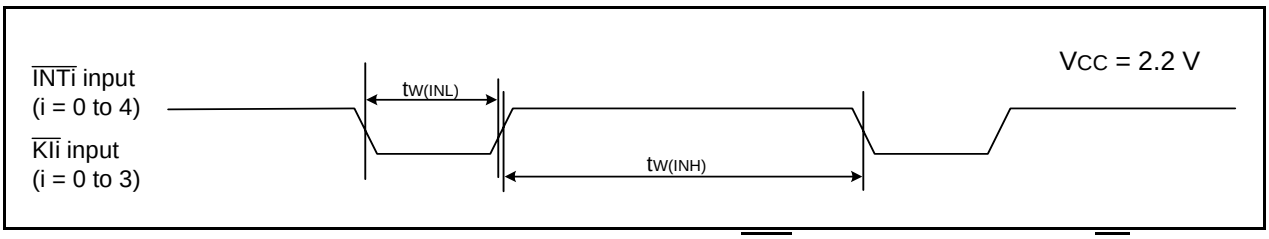
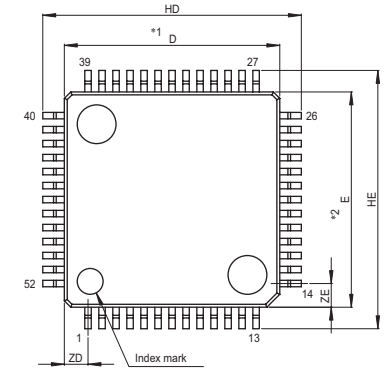


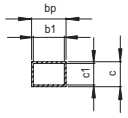
Figure 5.19 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 2.2 V

Package Dimensions

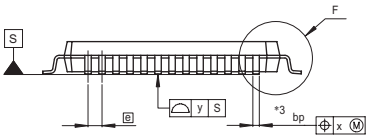
Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.

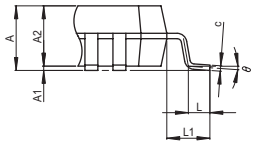
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP52-10x10-0.65	PLQP0052JA-A	52P6A-A	0.3g





Terminal cross section





Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.27	0.32	0.37
b_1	—	0.30	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
Z_D	—	1.1	—
Z_E	—	1.1	—
L	0.35	0.5	0.65
L_1	—	1.0	—